



60V 1.0mΩ N-Ch Power MOSFET

Features

- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge, Q_g
- 100% UIS and R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

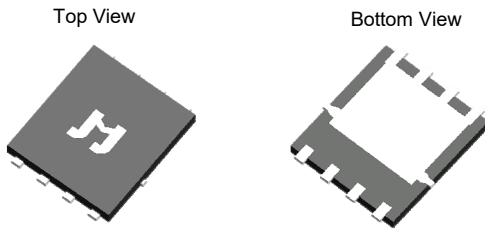
Product Summary

Parameter	Value	Unit
V_{DS}	60	V
$V_{GS(th_Typ)}$	2.8	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	303	A
$R_{DS(ON)_Typ}$ (@ $V_{GS} = 10V$)	1.0	mΩ

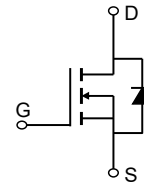
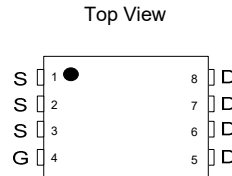
Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

PDFN5x6-8L



Pin Configuration

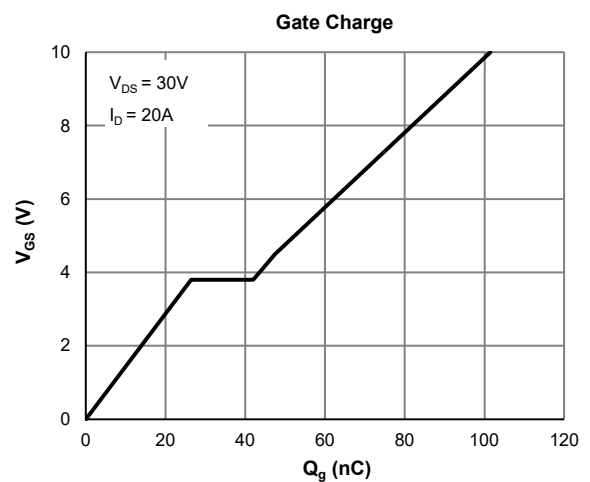
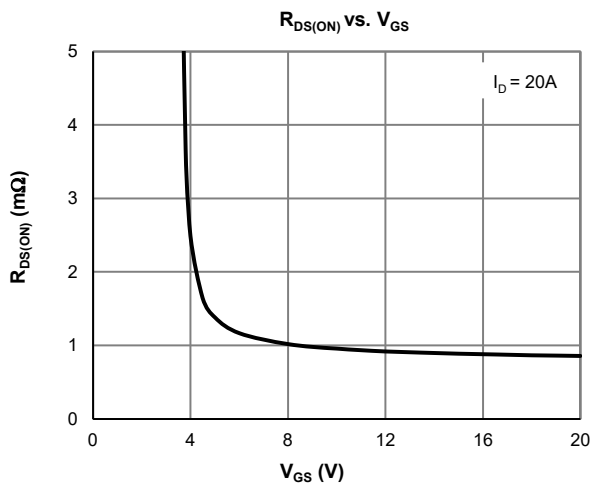


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH0601BG-13	PDFN5x6-8L	8	SH0601B	1	-55 to 150	13-inch Reel	3000

Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Gate-to-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ C$	303
		$T_C = 100^\circ C$	192
Pulsed Drain Current ⁽²⁾	I_{DM}	1213	A
Avalanche Energy ⁽³⁾	E_{AS}	1014	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ C$	179
		$T_C = 100^\circ C$	71
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C





Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.2	2.8	3.4	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		1.0	1.3	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		110		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.65	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			179	A

DYNAMIC PARAMETERS ⁽⁵⁾

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 30\text{V}, f = 1\text{MHz}$		7219		pF
Output Capacitance	C_{OSS}			1841		pF
Reverse Transfer Capacitance	C_{RSS}			47		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		3.3		Ω

SWITCHING PARAMETERS ⁽⁵⁾

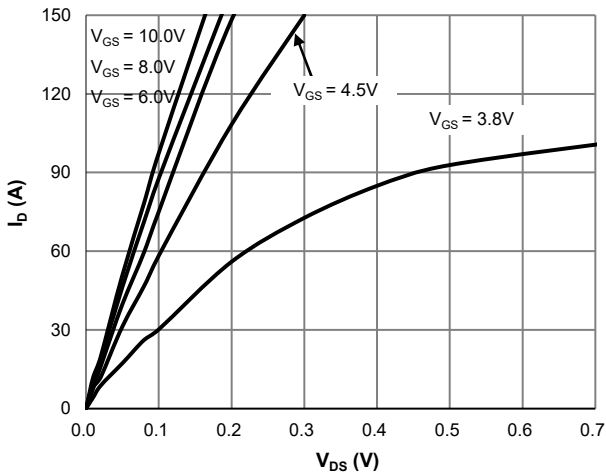
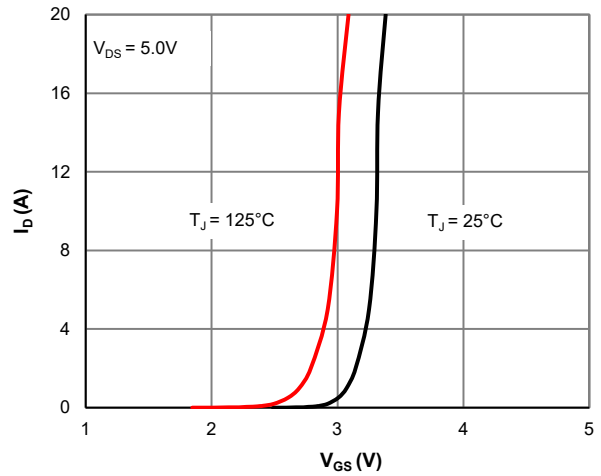
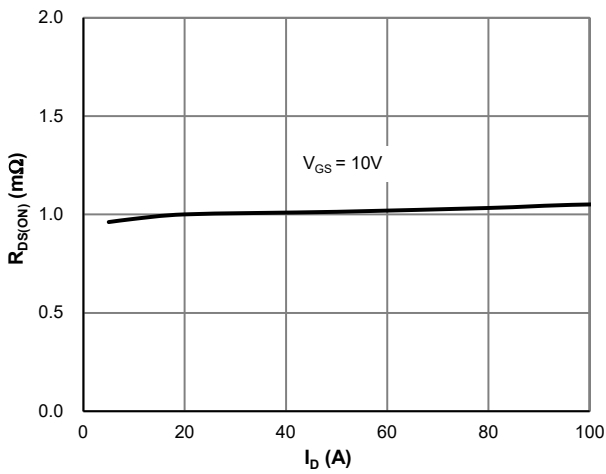
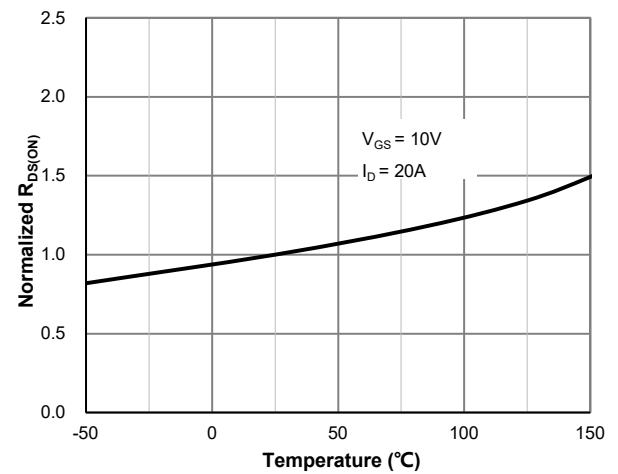
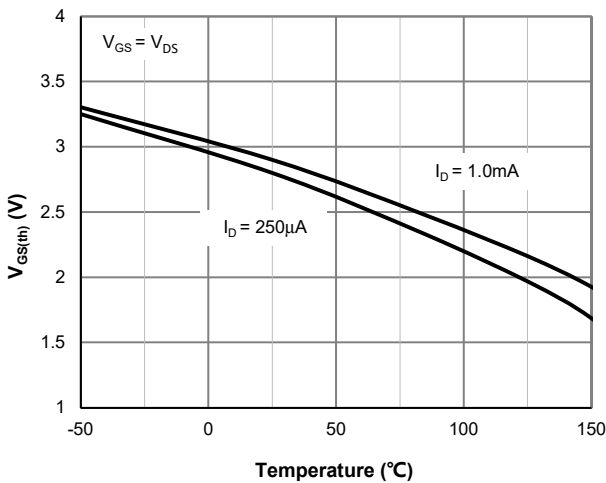
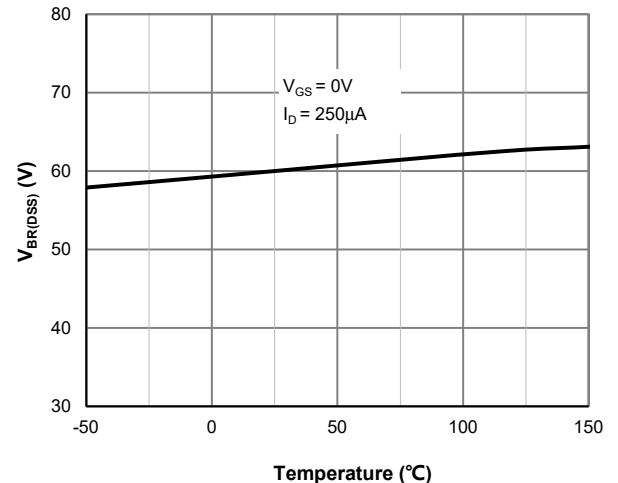
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 30\text{V}, I_D = 20\text{A}$		102		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			47		nC
Gate Source Charge	Q_{gs}			26		nC
Gate Drain Charge	Q_{gd}			15.6		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}$ $R_L = 1.5\Omega, R_{GEN} = 6\Omega$		84		ns
Turn-On Rise Time	t_r			25		ns
Turn-Off DelayTime	$t_{D(off)}$			131		ns
Turn-Off Fall Time	t_f			111		ns
Body Diode Reverse Recovery Time	t_{rr}		$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		71	
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		96		nC

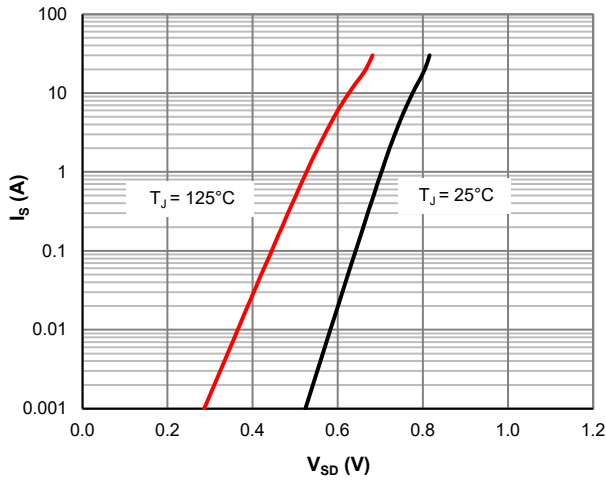
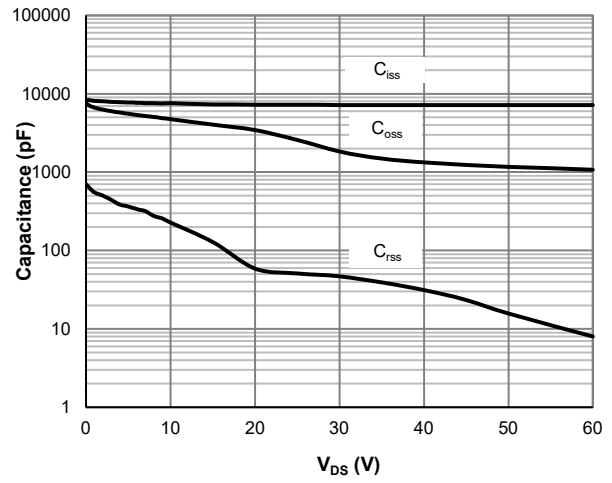
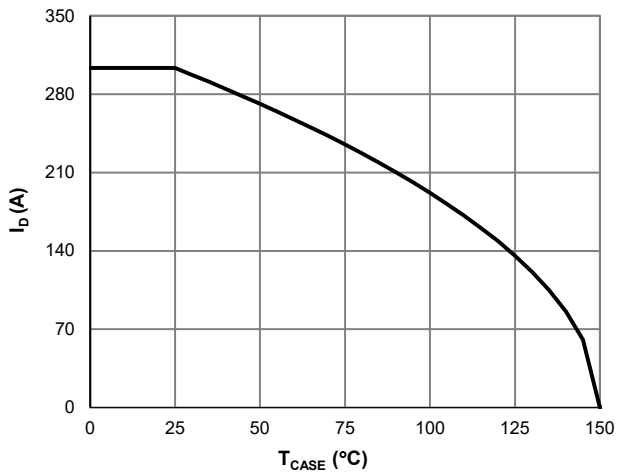
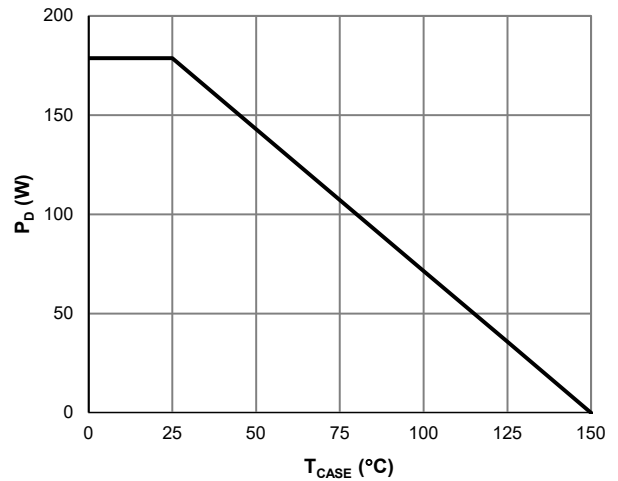
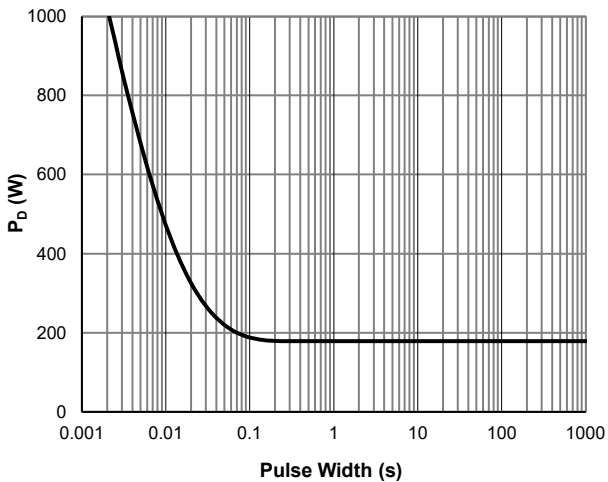
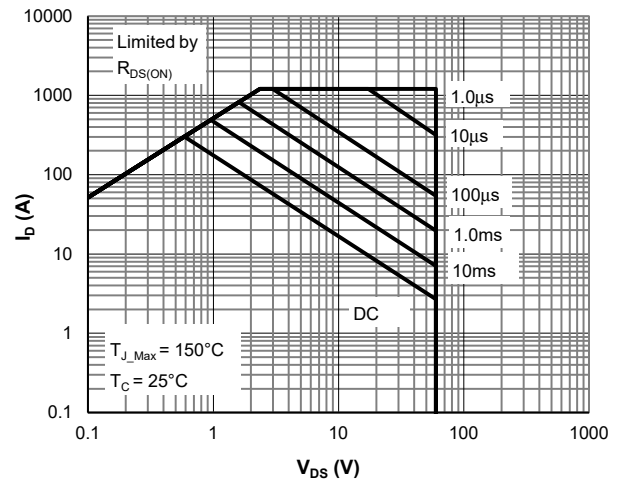
Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	40	48	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	0.85	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 1014 mJ is based on starting $T_J = 25^\circ\text{C}, L = 3.0\text{mH}, I_{AS} = 26\text{A}, V_{GS} = 10\text{V}, V_{DD} = 30\text{V}$; 100% test at $L = 0.6\text{mH}, I_{AS} = 45\text{A}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: $V_{GS(th)}$ vs. Junction Temperature

Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

Figure 7: Body-Diode Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Current De-rating

Figure 10: Power De-rating

Figure 11: Single Pulse Power Rating, Junction-to-Case

Figure 12: Maximum Safe Operating Area

Typical Electrical & Thermal Characteristics

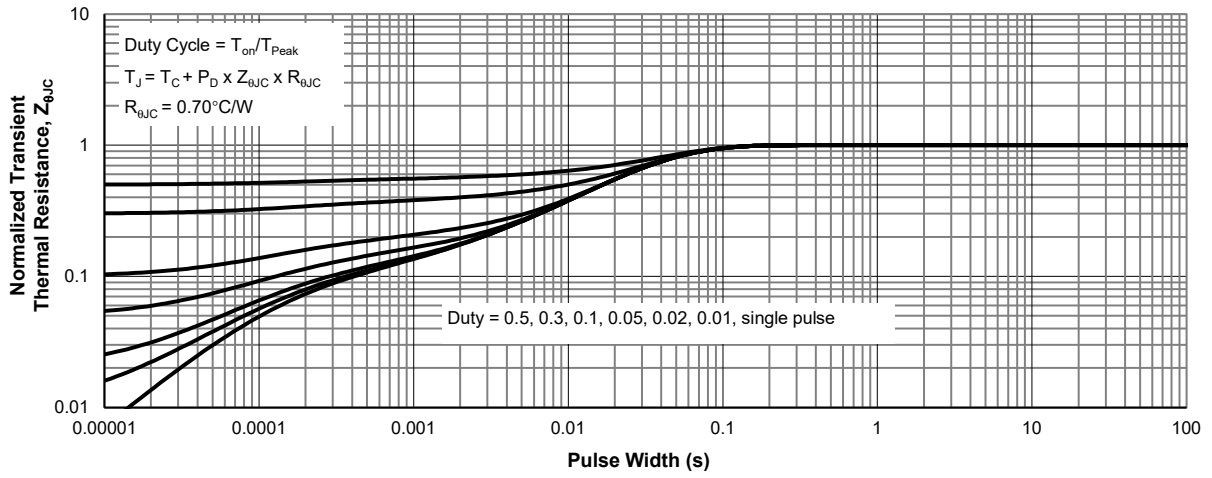


Figure 13: Normalized Maximum Transient Thermal Impedance

